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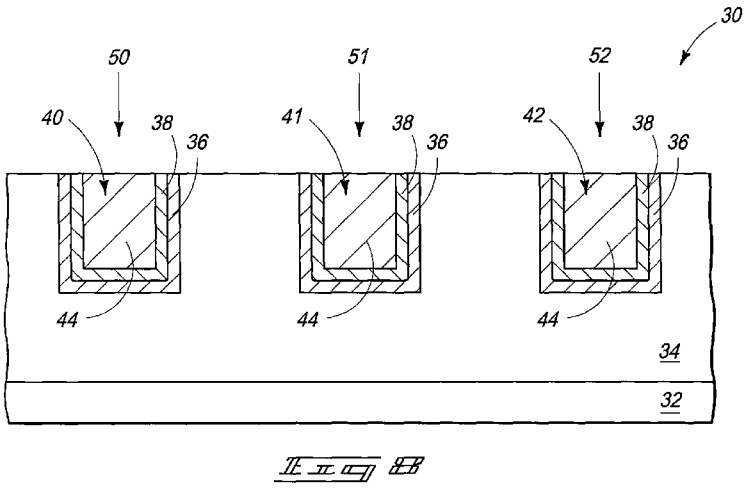


Fig. 8

(57) Abstract: Some embodiments include methods for depositing copper-containing material utilizing physical vapor deposition of the copper-containing material while keeping a temperature of the deposited copper-containing material at greater than 100°C. Some embodiments include methods in which openings are lined with a metal-containing composition, copper-containing material is physical vapor deposited over the metal- containing composition while a temperature of the copper-containing material is no greater than about 0°C, and the copper-containing material is then annealed while the copper-containing material is at a temperature in a range of from about 180°C to about 250°C. Some embodiments include methods in which openings are lined with a composition containing metal and nitrogen, and the lined openings are at least partially filled with copper-containing material. Some embodiments include semiconductor constructions having a metal nitride liner along sidewall peripheries of an opening, and having copper-containing material within the opening and directly against the metal nitride liner.

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